Title : Accurate junction capacitance model of the MOSFET for high-speed circuit simulator
Patent Number: 10063626
Author: Andy Huang...etc.
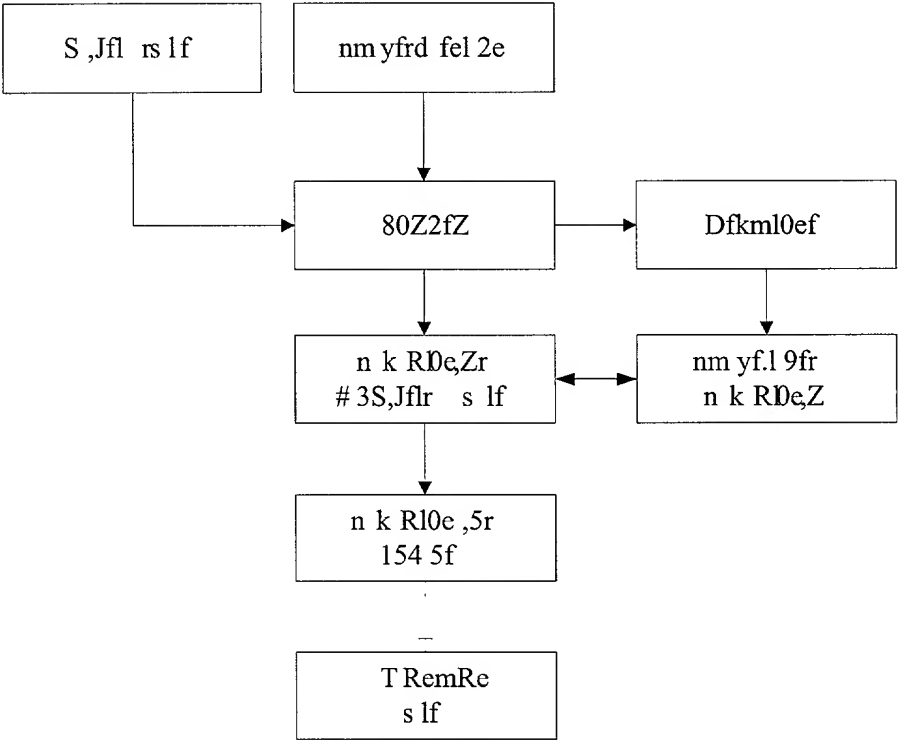
S ,Jfl rs 1f		nm yfrd fel 2e

80Z2fZ	→	Dfkml0ef

n k RlDe,Zr # 3S,Jflr s lf	↔	nm yf.l 9fr n k RlDe,Z

n k Rl0e ,5r 154 5f

T RemRe s lf

Figure 1

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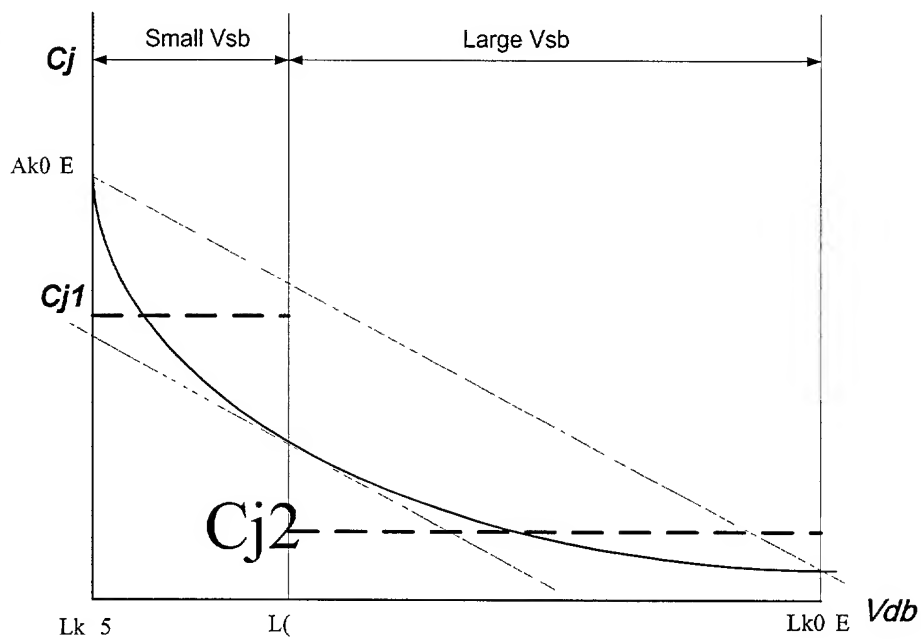Patent Number: 10063626
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Figure 2

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$$Cj1 = \frac{\int_{v\min}^{Vx} Cj\,dV}{V1 - V\min} \cong \frac{\sum_{i}^{vi \le v1} Cji}{V1 - V\min}$$

The corresponding value at the large region is $Cj2 = \dfrac{\int_{v1}^{v\max} Cj\,dv}{V\max - V1} \cong \dfrac{\sum_{i}^{Vi \le V\max} Cji}{V\max - V1}$

, which are modeled as Cj1, Cj2.

Figure 3